Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

# 2SK2836

# Chopper Regulator, DC-DC Converter and Motor Drive Applications

 $\begin{array}{ll} \bullet & Low\ drain-source\ ON\ resistance & \vdots\ R_{DS}\ (ON) = 6.4\ \Omega\ (typ.) \\ \bullet & High\ forward\ transfer\ admittance & \vdots\ |\ Y_{fs}\ | = 0.85\ S\ (typ.) \\ \bullet & Low\ leakage\ current & \vdots\ I_{DSS} = 100\ \mu A\ (max)\ (V_{DSS} = 600\ V) \\ \bullet & Enhancement-mode & \vdots\ V_{th} = 2.0 \\ \sim 4.0\ V\ (V_{DS} = 10\ V,\ I_D = 1\ mA) \end{array}$ 

### Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	600	V	
Drain-gate voltage (Ro	<sub>SS</sub> = 20 kΩ)	$V_{DGR}$	600	V	
Gate-source voltage		$V_{GSS}$	±30	V	
Drain current	DC (Note 1)	I <sub>D</sub>	1	Α	
	Pulse (Note 1)	I <sub>DP</sub>	2	Α	
Drain power dissipation	(Note 2)	P <sub>D</sub>	2.5	W	
Single pulse avalanche	e energy (Note 3)	E <sub>AS</sub>	56	mJ	
Avalanche current		I <sub>AR</sub>	1	Α	
Repetitive avalanche e	nergy (Note 4)	E <sub>AR</sub>	0.25	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature ra	ange	T <sub>stg</sub>	-55~150	°C	

# 1. GATE 2. DRAIN (HEAT SINK) 3. SOURCE JEDEC JETA

2-7H1B

Weight: 0.12 g (typ.)

### Marking

**TOSHIBA** 



### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	50	°C / W	

- Note 1: Please use devices on condition that the channel temperature is below 150°C.
- Note 2: Mounted on ceramic substrate (25.4 mm × 25.4 mm × 0.8 mm)
- Note 3:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 100 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 1 A
- Note 4: Repetitive rating; Pulse width limited by maximum channel temperature.

This transistor is an electrostatic sensitive device.

Please handle with caution.



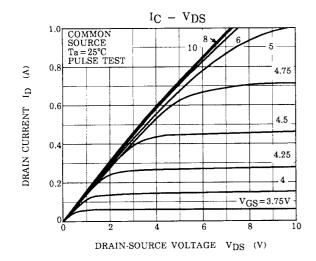
## Electrical Characteristics (Ta = 25°C)

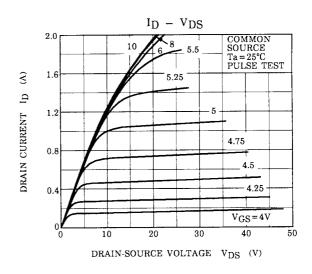
Charac	eteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0 V	_	_	±10	μΑ
Gate-source bro	eakdown voltage	V <sub>(BR)</sub> GSS	$I_{G} = \pm 10 \mu A, V_{DS} = 0 V$	±30	_	_	٧
Drain cut-off cu	rrent	I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	_	_	100	μA
Drain-source br	eakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	600	_	_	V
Gate threshold v	voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.0	_	4.0	٧
Drain-source O	N resistance	R <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 A	_	6.4	9.0	Ω
Forward transfe	r admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 A	0.4	0.85	_	S
Input capacitano	e	C <sub>iss</sub>		_	190	_	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	15	_	pF
Output capacitance		Coss			55	_	
Switching time	Rise time	t <sub>r</sub>	$V_{\rm GS}$ $0_{\rm V}$ $I_{\rm D}=0.5A$ $V_{\rm OUT}$ $R_{\rm L}=600\Omega$	_	12	_	
	Turn-on time	t <sub>on</sub>		_	55	_	20
	Fall time	t <sub>f</sub>		_	40	_	- ns
	Turn-off time	t <sub>off</sub>	$V_{DD} = 300V$ Duty $\leq 1\%$ , $t_w = 10 \mu s$	_	90	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	9	_	
Gate-source charge		$Q_{gs}$	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$		3.5	_	nC
Gate-drain ("miller") Charge		Q <sub>gd</sub>			5.5	_	

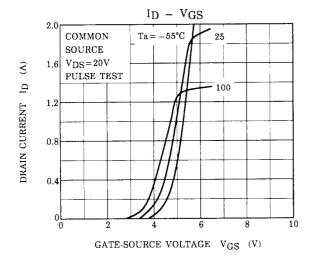
# Source-Drain Ratings and Characteristics (Ta = 25°C)

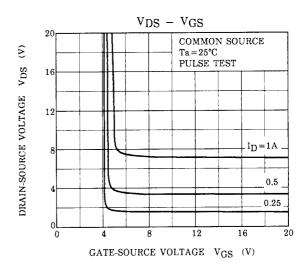
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	_	_	_	1	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	-	_	_	2	Α
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 1 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	$I_{DR} = 1 \text{ A}, V_{GS} = 0 \text{ V}, dI_{DR} / dt = 100 \text{ A} / \mu \text{s}$	_	400		ns
Reverse recovery charge	Q <sub>rr</sub>		_	1.4	_	μC

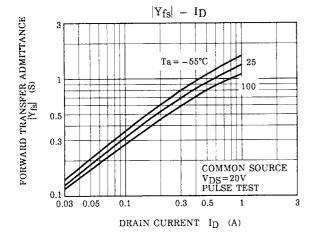
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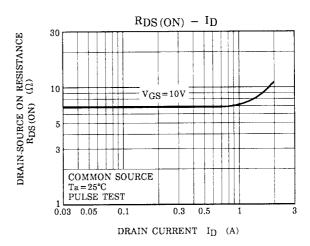


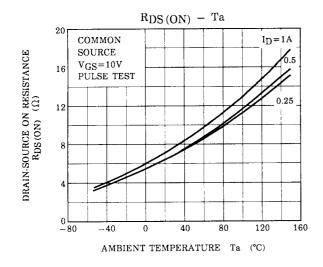


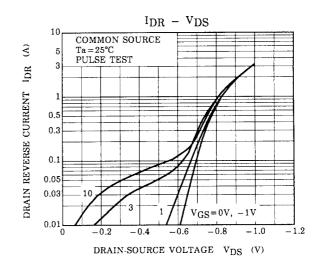


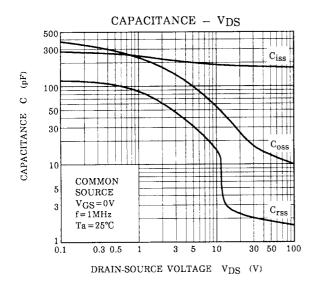


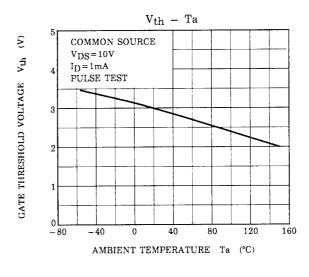


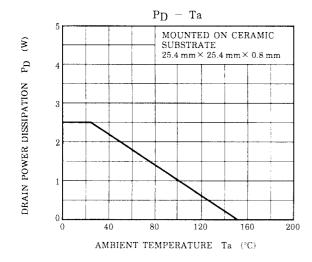


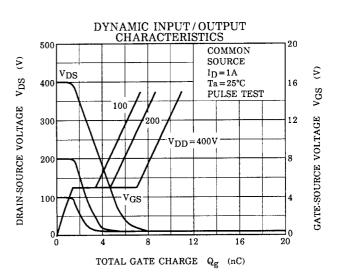




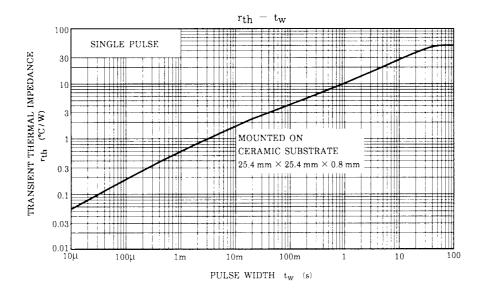


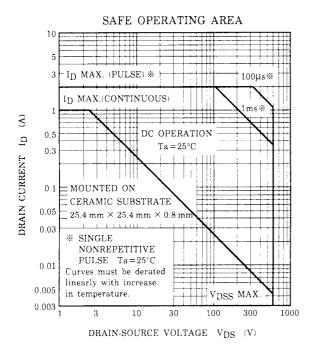


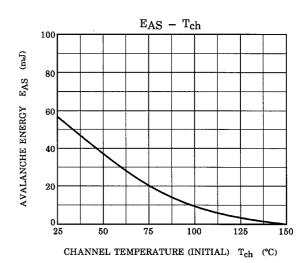


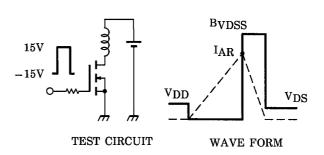


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$$R_G$$
 = 25  $\Omega$   
 $V_{DD}$  = 90 V, L = 100 mH

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^{2} \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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